

ABSTRACT OF THE DISCLOSURE

An N+ buried diffusion region is formed between a P- silicon substrate and an N- epitaxial layer and a P+ buried diffusion region is formed between the N+ buried diffusion region and the N- epitaxial layer. 5 An N diffusion region, a P diffusion region and an N diffusion region are formed in the surface for the N- epitaxial layer. The surface of the P+ buried diffusion region located, approximately, beneath the N diffusion region is recessed so as to go far away from the N diffusion region and a narrowed part is formed in this part. Thereby, in the OFF condition, the 10 depletion layer further extends in the part where the narrowed part is formed. As a result, the withstanding voltage of the semiconductor device is increased.